2060A

N-Channel Trench Power MOSFET

VDS=20V；ID=60A；
RDS(ON)<6.5mΩ @ VGS=4.5V
RDS(ON)<8.6mΩ @ VGS=2.5V

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Features

- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

Package



TO-252

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Absolute Maximum Ratings (T_C=25°Cunless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage (VGS=0V)	20	V
V_{GS}	Gate-Source Voltage (VDS=0V)	±12	V
I_D	Drain Current-Continuous(Tc=25°C)	60	A
	Drain Current-Continuous(Tc=100°C)	42	A
$I_{DM\ (pluse)}$	Drain Current-Continuous@ Current-Pulsed	202	A
P_D	Maximum Power Dissipation(Tc=25°C)	62	W
	Maximum Power Dissipation(Tc=100°C)	38	W
E_{AS}	Avalanche energy	216	mJ
T_J,T_{STG}	Operating Junction and Storage Temperature Range	-55 To 155	°C

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